

Amendments to the Claims:

The listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (Original) A process for forming an underlying film, comprising: irradiating the surface of an insulating film disposed on an electronic device substrate with plasma based on a process gas comprising at least an oxygen atom-containing gas, to thereby form an underlying film at the interface between the insulating film and the electronic device substrate.

2. (Original) A process for forming an underlying film according to claim 1, wherein the insulating film is a film comprising a high-k (high-dielectric constant) material.

3. (Currently Amended) A process for forming an underlying film according to claim 1 ~~or 2~~, wherein the plasma is plasma containing oxygen radicals.

4. (Currently Amended) A process for forming an underlying film according to ~~any one of claims 1 to 3~~ claim 1, wherein the underlying film is an oxide film.

5. (Currently Amended) A process for forming an underlying film according to ~~any one of claims 1 to 4~~claim 1, wherein the plasma is plasma based on a plane antenna member (RLSA).

6. (Original) An electronic device material, comprising: an electronic device substrate, an underlying film disposed on the substrate, and an insulating film disposed on the underlying film,

wherein the underlying film is a film which has been formed by supplying plasma from the insulating layer side.

7. (Original) The electronic device material according to claim 6, wherein the insulating film is a film comprising a high-k (high-dielectric constant) material.